

L Number	Hits	Search Text	DB	Time stamp
1	132	nanocrystalline and amorphous and silicon adj carbide	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/08/20 11:47
2	0	nanocrystalline near20 amorphous near20 silicon adj carbide	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/08/20 11:47
3	4	nanocrystalline same amorphous same silicon adj carbide	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/08/20 12:23

4	157	(US-6121633-\$ or US-6133587-\$ or US-6297521-\$ or US-6306691-\$ or US-6313482-\$ or US-6249020-\$ or US-6365919-\$ or US-6075259-\$ or US-5323040-\$ or US-6130147-\$ or US-5698869-\$ or US-5465249-\$ or US-4113515-\$ or US-4849797-\$ or US-4507673-\$ or US-6031263-\$ or US-5858811-\$ or US-6011279-\$ or US-6049110-\$ or US-5976926-\$ or US-4473836-\$ or US-5734181-\$ or US-6383576-\$ or US-5449941-\$ or US-5393999-\$ or US-5629222-\$).did. or (US-5801401-\$ or US-6166401-\$ or US-6018166-\$ or US-5989958-\$ or US-6180958-\$ or US-6344663-\$ or US-5886368-\$ or US-5039354-\$ or US-4826778-\$ or US-6163066-\$ or US-6084248-\$ or US-6099574-\$ or US-5260560-\$ or US-5159424-\$ or US-5056897-\$ or US-5451798-\$ or US-5369040-\$ or US-6166319-\$ or US-6093937-\$ or US-6144581-\$ or US-5539217-\$ or US-5371383-\$ or US-5719410-\$ or US-5661312-\$ or US-5672889-\$ or US-5798548-\$ or US-5506421-\$).did. or (US-6562131-\$ or US-6547877-\$ or US-6562130-\$ or US-6537371-\$ or US-5030580-\$ or US-4189826-\$ or US-5932902-\$ or US-4598305-\$ or US-5449925-\$ or US-5441901-\$ or US-6236590-\$ or US-4462150-\$ or US-4460670-\$ or US-4657699-\$ or US-5604357-\$ or US-5580380-\$ or US-5623442-\$ or US-5654208-\$ or US-5670790-\$ or US-5714766-\$ or US-5740104-\$ or US-5754477-\$ or US-5786250-\$ or US-5789276-\$ or US-5846859-\$ or US-5877041-\$ or US-5907775-\$).did. or (US-6034001-\$ or US-5886379-\$ or US-5557122-\$ or US-5866930-\$ or US-5808336-\$ or US-5508543-\$ or US-5898197-\$ or US-6351411-\$ or US-6178112-\$ or US-6205052-\$ or US-6197439-\$ or US-5640343-\$ or US-5793697-\$ or US-6166948-\$ or US-6307775-\$ or US-4451391-\$ or US-4768072-\$ or US-6309907-\$ or US-5061976-\$ or US-5625217-\$ or US-6002143-\$ or US-5852306-\$ or US-6108177-\$ or US-5408377-\$ or US-5145741-\$ or US-5235195-\$ or US-5260593-\$).did. or (US-5293560-\$ or US-5298796-\$ or US-5407845-\$ or US-5415126-\$ or US-5455432-\$ or US-5477485-\$ or US-5530581-\$ or US-5557114-\$ or US-5562769-\$ or US-4841349-\$ or US-4893273-\$ or US-5049950-\$ or US-5111430-\$ or US-4738729-\$ or US-4769686-\$).did. or (US-20010032997-\$ or US-20010049183-\$ or US-20020024050-\$ or US-20020137284-\$ or US-20020036331-\$ or US-20020017647-\$ or US-20020041514-\$ or US-20030001191-\$).did. or (EP-291951-\$ or EP-681333-\$ or US-5585986-\$).did. or (JP-63289960-\$ or JP-01115162-\$ or JP-63219172-\$ or JP-63181473-\$ or JP-62122275-\$ or JP-04056769-\$ or JP-03222367-\$ or JP-02203564-\$ or JP-56056677-\$ or JP-06302828-\$ or JP-07226507-\$ or JP-08255878-\$ or JP-60184681-\$ or JP-60242678-\$ or JP-08224431-\$ or JP-07120175-\$ or JP-04001170-\$).did. or	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/08/20 12:07
Search History 8/20/03 11:14:38 PM Page C:\APPS\EAST\Workspace\workspaces\096910401170-\$).did. or				

5	0	ultra-amorphous near6 nanocrystalline	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/08/20 12:08
6	0	ultra-amorphous	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/08/20 12:08
7	0	ultra adj amorphous	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/08/20 12:08
8	26	carbon adj gate	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/08/20 12:46
9	4	(carbon adj gate "carbon gate") and float\$3 near4 gate and control adj gate	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/08/20 13:04
10	2	("4598305").PN.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/08/20 13:04
11	2	("4994401").PN.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/08/20 13:04
-	13	((("4113515") or ("4473836") or ("5698869") or ("5858811") or ("5976926") or ("6031263") or ("6084248") or ("6093937") or ("6099574") or ("6130147") or ("6144581") or ("6163066") or ("6166401")).PN.	USPAT	2003/08/18 17:22
-	13	(US-6144581-\$ or US-6163066-\$ or US-6166401-\$ or US-4113515-\$ or US-4473836-\$ or US-5698869-\$ or US-5858811-\$ or US-5976926-\$ or US-6031263-\$ or US-6084248-\$ or US-6093937-\$ or US-6099574-\$ or US-6130147-\$).did.	USPAT	2002/05/10 11:29
-	1	hartstein.in. and low adj voltage adj memory.ti.	EPO	2002/05/10 11:28
-	0	jp-63289960\$-\$.did.	USPAT	2002/05/10 11:30
-	0	jp-363289960\$-\$.did.	USPAT	2002/05/10 11:30
-	0	jp-0363289960\$-\$.did.	USPAT	2002/05/10 11:34
-	1	takashi.in. and carrier near6 silicon adj substrate	USPAT	2002/05/10 11:36
-	3	takashi.in. and carrier near6 silicon adj substrate	JPO	2002/05/10 11:38
-	38	diamond adj layer near6 process	DERWENT	2002/05/10 11:39
-	2	(diamond adj layer near6 process) and silicon adj carbide	DERWENT	2002/05/10 11:45
-	1	takashi.in. and ito.in. and igfet	EPO	2002/05/10 11:45
-	0	jp-063219172\$-\$.did.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/10 11:47
-	2	jp-63219172\$-\$.did.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/10 12:15

-	2	jp-63289960\$-\$.did.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/05/10 11:49
-	2	jp-01115162\$-\$.did.	USPÄT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/05/10 11:49
-	2	jp-63181473\$-\$.did.	USPÄT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/05/10 11:50
-	2	jp-62122275\$-\$.did.	USPÄT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/05/10 11:51
-	0	jp-404056769\$-\$.did.	USPÄT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/05/10 11:52
-	2	jp-04056769\$-\$.did.	USPÄT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/05/10 12:02
-	796	(257/77).CCLS.	USPÄT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/05/10 14:04
-	9	((257/77).CCLS.) and (x near12 silicon adj carbide)	USPÄT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/05/10 12:18
-	489	silicon adj carbide and gate and x and source and drain	USPÄT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/05/10 12:19
-	53	silicon adj carbide.ti,ab. and gate and x and source and drain	USPÄT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/05/10 12:26
-	162	stoichiometric adj coefficient	USPÄT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/05/10 12:26
-	11	stoichiometric adj coefficient near x	USPÄT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/05/10 12:26
-	30	stoichiometric adj coefficient near12 x	USPÄT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/05/10 12:28
-	0	"si.sub.1-x.c.sub.x" and field adj effect adj transistor	USPÄT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/05/10 12:30

-	0	"si.sub.1-x.c.sub.x"	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/10 12:29
-	57	"si.sub.1-x" adj "c.sub.x"	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/10 12:31
-	18	"si.sub.1-x" adj "c.sub.x" and (mosfet or fet or nmosfet or pmosfet or field adj effect adj transistor or dtmosfet or gate)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/10 13:55
-	15	"si.sub.1-x" adj "c.sub.x" and (mosfet or fet or nmosfet or pmosfet or field adj effect adj transistor or dtmosfet or (gate and (source or drain)))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/10 13:57
-	179	((257/77).CCLS.) and (silicon carbide or "si.1-x. c.x." or "si.1-y. c.y." or "si.x. c.1-x" or "si.y. c.1-y") and x	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/10 14:07
-	50	((257/77).CCLS.) and (silicon carbide or "si.1-x. c.x." or "si.1-y. c.y." or "si.x. c.1-x" or "si.y. c.1-y") and x and (source same drain) and gate and (mosfet or nmosfet or pmosfet or dtmosfet or cmosfet or fet or field adj effect adj transistor)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/10 14:15
-	1	((257/77).CCLS.) and (silicon carbide or "si.1-x. c.x." or "si.1-y. c.y." or "si.x. c.1-x" or "si.y. c.1-y") and x and (source same drain) and gate and (mosfet or nmosfet or pmosfet or dtmosfet or cmosfet or fet or field adj effect adj transistor) and barrier adj energy	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/10 14:10
-	30	((257/77).CCLS.) and (silicon carbide or "si.1-x. c.x." or "si.1-y. c.y." or "si.x. c.1-x" or "si.y. c.1-y") and x and (source same drain) and gate and (mosfet or nmosfet or pmosfet or dtmosfet or cmosfet or fet or field adj effect adj transistor) and barrier	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/10 14:24
-	0	((257/77).CCLS.) and ("si.1-x. c.x." or "si.1-y. c.y." or "si.x. c.1-x" or "si.y. c.1-y") and x and (source same drain) and gate and (mosfet or nmosfet or pmosfet or dtmosfet or cmosfet or fet or field adj effect adj transistor) and barrier	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/10 14:26
-	0	((257/77).CCLS.) and ("si.1-x. c.x." or "si.1-y. c.y." or "si.x. c.1-x" or "si.y. c.1-y") and x and (source same drain) and gate and (mosfet or nmosfet or pmosfet or dtmosfet or cmosfet or fet or field adj effect adj transistor)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/10 14:20
-	0	("si.1-x. c.x." or "si.1-y. c.y." or "si.x. c.1-x" or "si.y. c.1-y") and x and (source same drain) and gate and (mosfet or nmosfet or pmosfet or dtmosfet or cmosfet or fet or field adj effect adj transistor)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/10 14:20
-	0	("si.1-x. c.x." or "si.1-y. c.y." or "si.x. c.1-x" or "si.y. c.1-y") and x and (mosfet or nmosfet or pmosfet or dtmosfet or cmosfet or fet or field adj effect adj transistor)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/10 14:20

-	0	((257/77).CCLS.) and ("si.1-x. c.x." or "si.1-y. c.y." or "si.x. c.1-x" or "si.y. c.1-y" or "si(x)c(1-x)" or "si(1-x)c(x)") and x and (source same drain) and gate and (mosfet or nmosfet or pmosfet or dtmosfet or cmosfet or fet or field adj effect adj transistor) and barrier	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/10 14:27
-	30	((257/77).CCLS.) and (silicon carbide or "si.1-x. c.x." or "si.1-y. c.y." or "si.x. c.1-x" or "si.y. c.1-y" or "si(x)c(1-x)" or "si(1-x)c(x)") and x and (source same drain) and gate and (mosfet or nmosfet or pmosfet or dtmosfet or cmosfet or fet or field adj effect adj transistor) and barrier	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/10 14:49
-	30	((257/77).CCLS.) and (silicon carbide or "si.1-x. c.x." or "si.1-y. c.y." or ("si.x. c.1-x" or "si.y. c.1-y" or "si(x)c(1-x)" or "si(1-x)c(x)") near12 gate) and x and (source same drain) and (mosfet or nmosfet or pmosfet or dtmosfet or cmosfet or fet or field adj effect adj transistor) and barrier	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/10 14:51
-	53	((257/77).CCLS.) and (silicon carbide or "si.1-x. c.x." or "si.1-y. c.y." or ("si.x. c.1-x" or "si.y. c.1-y" or "si(x)c(1-x)" or "si(1-x)c(x)") near12 gate) near12 x and (257/\$6.ccls. or 438/\$6.ccls. or 361/\$6.ccls.)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/10 14:52
-	2616	(silicon carbide or "si.1-x. c.x." or "si.1-y. c.y." or ("si.x. c.1-x" or "si.y. c.1-y" or "si(x)c(1-x)" or "si(1-x)c(x)") near12 gate) near12 x and (257/\$6.ccls. or 438/\$6.ccls. or 361/\$6.ccls.)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/10 14:53
-	133	(silicon adj carbide or "si.1-x. c.x." or "si.1-y. c.y." or ("si.x. c.1-x" or "si.y. c.1-y" or "si(x)c(1-x)" or "si(1-x)c(x)") near12 gate) near12 x and (257/\$6.ccls. or 438/\$6.ccls. or 361/\$6.ccls.)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/10 14:54
-	133	(silicon adj carbide or "si.1-x. c.x." or "si.1-y. c.y." or ("si.x. c.1-x" or "si.y. c.1-y" or "si(x)c(1-x)" or "si(1-x)c(x)") near6 gate) near12 x and (257/\$6.ccls. or 438/\$6.ccls. or 361/\$6.ccls.)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/10 14:55
-	2	((silicon adj carbide or "si.1-x. c.x." or "si.1-y. c.y." or "si.x. c.1-x" or "si.y. c.1-y" or "si(x)c(1-x)" or "si(1-x)c(x)") near6 gate) near12 x and (257/\$6.ccls. or 438/\$6.ccls. or 361/\$6.ccls.)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/10 15:05
-	0	((("si.1-x. c.x." or "si.1-y. c.y." or "si.x. c.1-x" or "si.y. c.1-y" or "si(x)c(1-x)" or "si(1-x)c(x)" or "si(a)c(1-a)" or "si(b)c(1-b)" or "si(1-a)c(a)" or "si(1-b)c(b)" or "si.a.c.1-a" or "si.1-a.c.a" or "si.b.c.1-b" or "si.1-b.c.b") near6 gate) near12 x and (257/\$6.ccls. or 438/\$6.ccls. or 361/\$6.ccls.)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/10 15:09
-	0	((("si.1-x. c.x." or "si.1-y. c.y." or "si.x. c.1-x" or "si.y. c.1-y" or "si(x)c(1-x)" or "si(1-x)c(x)" or "si(a)c(1-a)" or "si(b)c(1-b)" or "si(1-a)c(a)" or "si(1-b)c(b)" or "si.a.c.1-a" or "si.1-a.c.a" or "si.b.c.1-b" or "si.1-b.c.b") near12 gate) near12 (x or y or a or b) and (257/\$6.ccls. or 438/\$6.ccls. or 361/\$6.ccls.)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/10 18:35

-	1	((("si.1-x. c.x." or "si.1-y. c.y." or "si.x. c.1-x" or "si.y. c.1-y" or "si(x)c(1-x)" or "si(1-x)c(x)" or "si(a)c(1-a)" or "si(b)c(1-b)" or "si(1-a)c(a)" or "si(1-b)c(b)" or "si.a.c.1-a" or "si.1-a.c.a" or "si.b.c.1-b" or "si.1-b.c.b") near12 gate)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/10 15:12
-	684	(silicon adj carbide or sic or "si.1-x. c.x." or "si.1-y. c.y." or "si.x. c.1-x" or "si.y. c.1-y" or "si(x)c(1-x)" or "si(1-x)c(x)" or "si(a)c(1-a)" or "si(b)c(1-b)" or "si(1-a)c(a)" or "si(1-b)c(b)" or "si.a.c.1-a" or "si.1-a.c.a" or "si.b.c.1-b" or "si.1-b.c.b") near12 gate	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/10 15:13
-	161	((silicon adj carbide or sic or "si.1-x. c.x." or "si.1-y. c.y." or "si.x. c.1-x" or "si.y. c.1-y" or "si(x)c(1-x)" or "si(1-x)c(x)" or "si(a)c(1-a)" or "si(b)c(1-b)" or "si(1-a)c(a)" or "si(1-b)c(b)" or "si.a.c.1-a" or "si.1-a.c.a" or "si.b.c.1-b" or "si.1-b.c.b") near6 gate) and 257/\$6.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/10 18:42
-	2	("6249020").PN.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/10 16:24
-	2	("6031263").PN.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/10 17:09
-	2	("6049110").PN.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/10 17:09
-	0	((("si.1-x. c.x." or "si.1-y. c.y." or "si.x. c.1-x" or "si.y. c.1-y" or "si(x)c(1-x)" or "si(1-x)c(x)" or "si(a)c(1-a)" or "si(b)c(1-b)" or "si(1-a)c(a)" or "si(1-b)c(b)" or "si.a.c.1-a" or "si.1-a.c.a" or "si.b.c.1-b" or "si.1-b.c.b") near6 gate) and 257/\$6.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/10 18:33
-	0	((("si.1-x. c.x." or "si.1-y. c.y." or "si.x. c.1-x" or "si.y. c.1-y" or "si(x)c(1-x)" or "si(1-x)c(x)" or "si(a)c(1-a)" or "si(b)c(1-b)" or "si(1-a)c(a)" or "si(1-b)c(b)" or "si.a.c.1-a" or "si.1-a.c.a" or "si.b.c.1-b" or "si.1-b.c.b") near6 gate)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/10 18:33

-	51	(US-5451798-\$ or US-6166319-\$ or US-4113515-\$ or US-4473836-\$ or US-5698869-\$ or US-5858811-\$ or US-5976926-\$ or US-6031263-\$ or US-6084248-\$ or US-6093937-\$ or US-6099574-\$ or US-6130147-\$ or US-6144581-\$ or US-6163066-\$ or US-6166401-\$ or US-5661312-\$ or US-5719410-\$ or US-5798548-\$ or US-5801401-\$ or US-6011279-\$ or US-6049110-\$ or US-6306691-\$ or US-6313482-\$ or US-6365919-\$ or US-6249020-\$ or US-6344663-\$).did. or (US-5886368-\$ or US-6383576-\$ or US-4826778-\$ or US-5039354-\$ or US-5056897-\$ or US-5159424-\$ or US-5260560-\$ or US-5369040-\$).did. or (US-20010032997-\$ or US-20010049183-\$).did. or (EP-681333-\$ or EP-291951-\$).did. or (JP-04056769-\$ or JP-62122275-\$ or JP-63181473-\$ or JP-01115162-\$ or JP-63219172-\$ or JP-63289960-\$ or JP-56056677-\$).did. or (JP-04056769-\$ or JP-62122275-\$ or EP-276002-\$ or EP-291951-\$ or JP-01115162-\$ or JP-07115191-\$).did.	USPAT; US-PGPUB; EPO; JPO; DERWENT	2002/05/10 18:34
-	351	silicon near3 doped near6 carbon	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/10 18:36
-	45	(silicon near3 doped near6 carbon) and (257/\$6.ccls. or 438/\$6.ccls.) and gate	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/10 18:38
-	4	((silicon near3 doped near6 carbon) near12 gate) and (257/\$6.ccls. or 438/\$6.ccls.)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/10 18:40
-	5	((silicon near3 dop\$3 near6 carbon) near12 gate) and (257/\$6.ccls. or 438/\$6.ccls.)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/10 18:41
-	235	((carbon or silicon adj carbide or sic or "si.l-x. c.x." or "si.l-y. c.y." or "si.x. c.l-x" or "si.y. c.l-y" or "si(x)c(1-x)" or "si(1-x)c(x)" or "si(a)c(1-a)" or "si(b)c(1-b)" or "si(1-a)c(a)" or "si(1-b)c(b)" or "si.a.c.l-a" or "si.l-a.c.a" or "si.b.c.l-b" or "si.l-b.c.b") near6 gate) and 257/\$6.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/10 18:43
-	74	((carbon or silicon adj carbide or sic or "si.l-x. c.x." or "si.l-y. c.y." or "si.x. c.l-x" or "si.y. c.l-y" or "si(x)c(1-x)" or "si(1-x)c(x)" or "si(a)c(1-a)" or "si(b)c(1-b)" or "si(1-a)c(a)" or "si(1-b)c(b)" or "si.a.c.l-a" or "si.l-a.c.a" or "si.b.c.l-b" or "si.l-b.c.b") near6 gate) and 257/\$6.ccls.) not (((silicon adj carbide or sic or "si.l-x. c.x." or "si.l-y. c.y." or "si.x. c.l-x" or "si.y. c.l-y" or "si(x)c(1-x)" or "si(1-x)c(x)" or "si(a)c(1-a)" or "si(b)c(1-b)" or "si(1-a)c(a)" or "si(1-b)c(b)" or "si.a.c.l-a" or "si.l-a.c.a" or "si.b.c.l-b" or "si.l-b.c.b") near6 gate) and 257/\$6.ccls.)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/10 20:13

-	0	silicon-doped adj carbon adj (film or electrode)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/05/10 20:13
-	0	si-doped adj carbon adj (film or electrode)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/05/10 20:14
-	201	(( c or carbon) near (si or silicon)) adj (film or electrode)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/05/10 20:15
-	10092	(( c or carbon) near6 (si or silicon)) near6 (film or electrode)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/05/10 20:16
-	3434	(carbon near6 (si or silicon)) near6 (film or electrode)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/05/10 20:16
-	118	(carbon near1 (si or silicon)) near3 (film or electrode) and (257/\$6.ccls. or 438/\$6.ccls.)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/05/10 21:21
-	0	polysilicon/carbon near12 gate adj electrode	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/05/10 21:22
-	0	"polysilicon/carbon" near12 gate adj electrode	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/05/10 21:22
-	0	(polysilicon near1 carbon) near12 gate adj electrode	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/05/10 21:23
-	1	(silicon near1 carbon) near12 gate adj electrode	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/05/10 21:49
-	6	p-doped adj silicon adj carbide	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/05/10 21:30
-	7	P-dopant near12 carbon	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/05/10 21:49
-	0	carbon adj doping adj2 silicon adj carbide	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/05/11 16:21
-	4	silicon adj doping adj2 carbon	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/05/11 16:27

-	0	p-doped adj silicon adj carbon	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/05/11 16:27
-	7	p-doped adj2 silicon adj2 carbon	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/05/11 16:28
-	1	(p-doped or p-doping) near12 silicon adj carbon	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/05/11 16:31
-	0	"si.sub.1-x.c.sub.x"	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/05/11 16:35
-	57	"si.sub.1-x c.sub.x"	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/05/11 16:43
-	0	"si.sub.1-x c.sub.x" near20 (work adj function or workfunction)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/05/11 16:43
-	2	"si.sub.1-x c.sub.x" near20 (barrier or work adj function or workfunction)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/05/11 16:48
-	1	"si.sub.x c.sub.1-x" near20 (barrier or work adj function or workfunction)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/05/11 16:49
-	10	"si.sub.1-x c.sub.x" near20 (electrode or conductivity or conduction)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/05/11 17:04
-	1	("si.sub.1-x c.sub.x" or "si.sub.x c.sub.1-x" or "si.sub.1-y c.sub.y" or "si.sub.y c.sub.1-y") near20 electron adj affinity	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/05/11 20:09
-	0	resistivity near4 "si.sub.1-x. c.x"	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/05/11 20:26
-	965	(conductivity or resistivity) near12 silicon adj carbide	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/05/11 20:39
-	0	(conductivity or resistivity) near12 "si.sub.1-x c.x"	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/05/11 21:10
-	8	barrier adj energy near12 silicon adj dioxide	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/05/11 21:14

-	0	barrier adj energy near12 silicon adj carbide	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/11 21:20
-	108	barrier adj energy.ti,ab.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/11 21:23
-	2	barrier adj energy near12 (sic or "si.sub.1-x. c.x" or silicon adj carbide)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/11 21:24
-	21	(resistivity or conductivity) near12 (silicon adj carbide or "si.sub.1-x. c.sub.x" or "si.sub.x. c.sub.1-x") near12 x	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/12 12:26
-	17	barrier adj energy near12 gate near12 insulator	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/12 12:07
-	3	("5661312").PN.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/12 12:10
-	0	("floating adj gate and control adj gate and silicon adj dioxide and (sic or silicon adj carbide)").PN.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/12 12:10
-	30	floating adj gate and control adj gate and silicon adj dioxide and (sic or silicon adj carbide)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/12 12:11
-	0	floating adj gate and control adj gate and silicon adj dioxide and (sic or silicon adj carbide) and photodetection	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/12 12:12
-	30	floating adj gate and control adj gate and silicon adj dioxide and (sic or silicon adj carbide) and memory	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/12 12:21
-	18	floating adj gate and control adj gate and silicon adj dioxide and (sic or silicon adj carbide) and memory and barrier	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/12 12:21
-	18	floating adj gate and control adj gate and silicon adj dioxide and (sic or silicon adj carbide) and memory and (barrier adj energy or potential adj barrier or tunneling adj barrier or interface adj barrier or barrier)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/12 12:23
-	3	("5886368").PN.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/12 17:44
-	3	("5661312").PN.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/12 17:46

-	46061	polycrystalline near12 silicon carbide and (mosfet or fet or nmosfet or pmosfet or cmosfet or field ajd effect adj transistor) and (memory or photodetect\$3)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/05/12 17:48
-	13	polycrystalline near12 silicon adj carbide and (mosfet or fet or nmosfet or pmosfet or cmosfet or field ajd effect adj transistor) and (memory or photodetect\$3)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/05/12 17:50
-	22	(polycrystalline or monocrystalline) near12 silicon adj carbide and (mosfet or fet or nmosfet or pmosfet or cmosfet or field ajd effect adj transistor) and (memory or photodetect\$3)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/05/12 17:51
-	4	(polycrystalline or monocrystalline) near12 silicon adj carbide near12 gate and (mosfet or fet or nmosfet or pmosfet or cmosfet or field ajd effect adj transistor) and (memory or photodetect\$3)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/05/12 17:52
-	24	(polycrystalline or monocrystalline) near12 silicon adj carbide near12 gate	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/05/12 18:16
-	3	("5369040").PN.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/05/12 18:17
-	10	floating adj gate near12 control adj gate and photodetect\$3 and (mosfet or cmos or cmosfet or nmos or nmosfet or pmos or pmosfet or transistor or field adj effect)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/05/12 18:30
-	0	floating adj gate near12 control adj gate near12 silicon adj carbide and photodetect\$3 and (mosfet or cmos or cmosfet or nmos or nmosfet or pmos or pmosfet or transistor or field adj effect)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/05/12 18:31
-	0	floating adj gate near12 control adj gate near12 silicon adj carbide and photodetect\$3	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/05/12 18:31
-	0	floating adj gate near12 control adj gate near12 silicon adj carbide	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/05/12 18:32
-	2	floating adj gate near12 control adj gate near12 (sic or silicon adj carbide or "si.sub.1-x. c.sub.x")	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/05/12 18:56
-	2	("5989958").PN.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/05/12 19:00
-	3	("5801401").PN.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/05/12 19:33
-	2	("5808336").PN.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/05/12 19:43

-	3	("5801401").PN.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/05/12 19:43
-	3	("4473836").PN.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/05/13 10:06
-	2	("5808336").PN.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/05/13 10:11
-	3	("5801401").PN.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/05/13 11:25
-	0	floating adj gate and control adj gate and source same drain and silcion adj carbide and silicon adj substrate and channel	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/05/13 11:26
-	41	floating adj gate and control adj gate and source same drain and silicon adj carbide and silicon adj substrate and channel	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/05/13 11:27
-	41	floating adj gate and control adj gate and source same drain and silicon adj carbide and silicon adj substrate and channel and (memory or photodetect\$3)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/05/13 12:16
-	74	crystalline near12 floating adj gate	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/05/13 12:16
-	37	crystalline near3 floating adj gate	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/05/13 13:21
-	5	((("5661312") or ("5798548") or ("5989958") or ("5369040") or ("5557122"))).PN.	USPAT	2002/05/13 16:23
-	47	hamakawa.in. and carbide	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/05/13 16:13
-	24	hamakawa.in. and carbide	JPO	2002/05/13 16:13
-	1	("5808336").PN.	USPAT	2002/05/13 17:16

-	52	((("4460670") or ("4462150") or ("4507673") or ("4657699") or ("4738729") or ("4768072") or ("4769686") or ("4841349") or ("4849797") or ("4893273") or ("5049950") or ("5111430") or ("5145741") or ("5235195") or ("5260593") or ("5293560") or ("5298796") or ("5369040") or ("5371383") or ("5407845") or ("5415126") or ("5449941") or ("5455432") or ("5465249") or ("5477485") or ("5508543") or ("5530581") or ("5557114") or ("5562769") or ("5580380") or ("5604357") or ("5623442") or ("5629222") or ("5654208") or ("5670790") or ("5714766") or ("5719410") or ("5740104") or ("5754477") or ("5786250") or ("5789276") or ("5801401") or ("5846859") or ("5877041") or ("5886368") or ("5886379") or ("5898197") or ("5907775") or ("6018166") or ("6031263") or ("6034001") or ("6075259")).PN.	USPAT	2002/05/13 17:30
-	6	((("4460670") or ("4462150") or ("4507673") or ("4657699") or ("4738729") or ("4768072") or ("4769686") or ("4841349") or ("4849797") or ("4893273") or ("5049950") or ("5111430") or ("5145741") or ("5235195") or ("5260593") or ("5293560") or ("5298796") or ("5369040") or ("5371383") or ("5407845") or ("5415126") or ("5449941") or ("5455432") or ("5465249") or ("5477485") or ("5508543") or ("5530581") or ("5557114") or ("5562769") or ("5580380") or ("5604357") or ("5623442") or ("5629222") or ("5654208") or ("5670790") or ("5714766") or ("5719410") or ("5740104") or ("5754477") or ("5786250") or ("5789276") or ("5801401") or ("5846859") or ("5877041") or ("5886368") or ("5886379") or ("5898197") or ("5907775") or ("6018166") or ("6031263") or ("6034001") or ("6075259")).PN.) and ("si.sub.1-x. c.sub.x" or "si.sub.1-y. c.sub.y" or "si.sub.x c.sub.1-x" or "si.sub.y c.sub.1-y" or silicon carbide or sic) and source and drain and floating adj gate and control adj gate and silicon adj dioxide	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/13 18:18

-	0	((("4460670") or ("4462150") or ("4507673") or ("4657699") or ("4738729") or ("4768072") or ("4769686") or ("4841349") or ("4849797") or ("4893273") or ("5049950") or ("5111430") or ("5145741") or ("5235195") or ("5260593") or ("5293560") or ("5298796") or ("5369040") or ("5371383") or ("5407845") or ("5415126") or ("5449941") or ("5455432") or ("5465249") or ("5477485") or ("5508543") or ("5530581") or ("5557114") or ("5562769") or ("5580380") or ("5604357") or ("5623442") or ("5629222") or ("5654208") or ("5670790") or ("5714766") or ("5719410") or ("5740104") or ("5754477") or ("5786250") or ("5789276") or ("5801401") or ("5846859") or ("5877041") or ("5886368") or ("5886379") or ("5898197") or ("5907775") or ("6018166") or ("6031263") or ("6034001") or ("6075259")).PN.) and ("si.sub.1-x. c.sub.x" or "si.sub.1-y. c.sub.y" or "si.sub.x c.sub.1-x" or "si.sub.y c.sub.1-y") and source and drain and floating adj gate and control adj gate and silicon adj dioxide	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/13 20:34
-	588	(257/77).CCLS.	USPAT; US-PGPUB	2002/05/13 20:34
-	118	(257/153).CCLS.	USPAT; US-PGPUB	2002/05/13 20:34
-	402	(257/314).CCLS.	USPAT; US-PGPUB	2002/05/13 20:39
-	782	(257/315).CCLS.	USPAT; US-PGPUB	2002/05/13 20:39
-	943	(257/316).CCLS.	USPAT; US-PGPUB	2002/05/13 20:40
-	2311	((257/77).CCLS.) or ((257/153).CCLS.) or ((257/314).CCLS.) or ((257/315).CCLS.) or ((257/316).CCLS.)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/13 20:40
-	357	((257/77).CCLS.) or ((257/153).CCLS.) or ((257/314).CCLS.) or ((257/315).CCLS.) or ((257/316).CCLS.)) and silicon adj carbide	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/13 20:44
-	90	((257/77).CCLS.) or ((257/153).CCLS.) or ((257/314).CCLS.) or ((257/315).CCLS.) or ((257/316).CCLS.)) and (silicon adj carbide near15 gate)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/13 21:12
-	2	("5989958").PN.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/13 21:12

-	115	(US-5449941-\$ or US-5455432-\$ or US-5039354-\$ or US-5056897-\$ or US-5159424-\$ or US-5260560-\$ or US-5369040-\$ or US-5451798-\$ or US-5734181-\$ or US-6166319-\$ or US-6383576-\$ or US-5801401-\$ or US-5989958-\$ or US-6344663-\$ or US-4113515-\$ or US-4473836-\$ or US-5698869-\$ or US-5858811-\$ or US-5976926-\$ or US-6031263-\$ or US-6084248-\$ or US-6093937-\$ or US-6099574-\$ or US-6130147-\$ or US-6144581-\$ or US-6163066-\$).did. or (US-6166401-\$ or US-5465249-\$ or US-4451391-\$ or US-6309907-\$ or US-5061976-\$ or US-5625217-\$ or US-5661312-\$ or US-5798548-\$ or US-6011279-\$ or US-6049110-\$ or US-6249020-\$ or US-6306691-\$ or US-6313482-\$ or US-6365919-\$ or US-5719410-\$ or US-5886368-\$ or US-4826778-\$ or US-6351411-\$ or US-5557114-\$ or US-5562769-\$ or US-5580380-\$ or US-5604357-\$ or US-5623442-\$ or US-5629222-\$ or US-5654208-\$ or US-5670790-\$ or US-5714766-\$).did. or (US-5740104-\$ or US-5754477-\$ or US-5786250-\$ or US-5789276-\$ or US-5846859-\$ or US-5877041-\$ or US-5886379-\$ or US-5907775-\$ or US-6018166-\$ or US-6034001-\$ or US-6075259-\$ or US-5557122-\$ or US-5866930-\$ or US-5898197-\$ or US-5808336-\$ or US-5393999-\$ or US-5539217-\$ or US-4460670-\$ or US-4462150-\$ or US-4507673-\$ or US-4657699-\$ or US-4738729-\$ or US-4768072-\$ or US-4769686-\$ or US-4841349-\$ or US-4849797-\$ or US-4893273-\$).did. or (US-5049950-\$ or US-5111430-\$ or US-5145741-\$ or US-5235195-\$ or US-5260593-\$ or US-5293560-\$ or US-5298796-\$ or US-5371383-\$ or US-5407845-\$ or US-5415126-\$ or US-5508543-\$ or US-5530581-\$ or US-5477485-\$).did. or (US-20010032997-\$ or US-20010049183-\$ or US-20020024050-\$ or US-20020017647-\$).did. or (EP-291951-\$ or EP-681333-\$).did. or (JP-62122275-\$ or JP-63181473-\$ or JP-01115162-\$ or JP-63219172-\$ or JP-04056769-\$ or JP-63289960-\$ or JP-57126175-\$ or JP-04061170-\$ or JP-56056677-\$ or JP-02203564-\$).did. or (JP-04056769-\$ or JP-62122275-\$ or JP-01115162-\$ or EP-291951-\$ or EP-276002-\$ or JP-07115191-\$).did.	USPAT; US-PGPUB; EPO; JPO; DERWENT	2002/05/14 08:24
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-	1	((US-5449941-\$ or US-5455432-\$ or US-5039354-\$ or US-5056897-\$ or US-5159424-\$ or US-5260560-\$ or US-5369040-\$ or US-5451798-\$ or US-5734181-\$ or US-6166319-\$ or US-6383576-\$ or US-5801401-\$ or US-5989958-\$ or US-6344663-\$ or US-4113515-\$ or US-4473836-\$ or US-5698869-\$ or US-5858811-\$ or US-5976926-\$ or US-6031263-\$ or US-6084248-\$ or US-6093937-\$ or US-6099574-\$ or US-6130147-\$ or US-6144581-\$ or US-6163066-\$).did. or (US-6166401-\$ or US-5465249-\$ or US-4451391-\$ or US-6309907-\$ or US-5061976-\$ or US-5625217-\$ or US-5661312-\$ or US-5798548-\$ or US-6011279-\$ or US-6049110-\$ or US-6249020-\$ or US-6306691-\$ or US-6313482-\$ or US-6365919-\$ or US-5719410-\$ or US-5886368-\$ or US-4826778-\$ or US-6351411-\$ or US-5557114-\$ or US-5562769-\$ or US-5580380-\$ or US-5604357-\$ or US-5623442-\$ or US-5629222-\$ or US-5654208-\$ or US-5670790-\$ or US-5714766-\$).did. or (US-5740104-\$ or US-5754477-\$ or US-5786250-\$ or US-5789276-\$ or US-5846859-\$ or US-5877041-\$ or US-5886379-\$ or US-5907775-\$ or US-6018166-\$ or US-6034001-\$ or US-6075259-\$ or US-5557122-\$ or US-5866930-\$ or US-5898197-\$ or US-5808336-\$ or US-5393999-\$ or US-5539217-\$ or US-4460670-\$ or US-4462150-\$ or US-4507673-\$ or US-4657699-\$ or US-4738729-\$ or US-4768072-\$ or US-4769686-\$ or US-4841349-\$ or US-4849797-\$ or US-4893273-\$).did. or (US-5049950-\$ or US-5111430-\$ or US-5145741-\$ or US-5235195-\$ or US-5260593-\$ or US-5293560-\$ or US-5298796-\$ or US-5371383-\$ or US-5407845-\$ or US-5415126-\$ or US-5508543-\$ or US-5530581-\$ or US-5477485-\$).did. or (US-20010032997-\$ or US-20010049183-\$ or US-20020024050-\$ or US-20020017647-\$).did. or (EP-291951-\$ or EP-681333-\$).did. or (JP-62122275-\$ or JP-63181473-\$ or JP-01115162-\$ or JP-63219172-\$ or JP-04056769-\$ or JP-63289960-\$ or JP-57126175-\$ or JP-04061170-\$ or JP-56056677-\$ or JP-02203564-\$).did. or (JP-04056769-\$ or JP-62122275-\$ or JP-01115162-\$ or EP-291951-\$ or EP-276002-\$ or JP-07115191-\$).did.) and ohba.in. (257/77).CCLS.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/14 08:34
-	799		USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/14 08:53
-	2	("5989958").PN.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/14 10:54

-	469	(257/314).CCLS.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/05/14 09:08
-	467	((257/314).CCLS.) not ((257/77).CCLS.)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/05/14 09:24
-	1816	257/315	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/05/14 09:24
-	1577	(257/315 not (((257/314).CCLS.) not ((257/77).CCLS.))) not ((257/77).CCLS.)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/05/14 09:26
-	1375	(257/316).CCLS.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/05/14 10:54
-	858	((((257/316).CCLS.) not 257/315) not (((257/314).CCLS.) not ((257/77).CCLS.))) not ((257/77).CCLS.)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/05/14 10:55
-	0	("jp-3222367\$-\$\$.did.").PN.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/05/14 12:45
-	2	jp-03222367\$-\$\$.did.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/05/14 12:46
-	13	jp-0224431\$-\$\$.did.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/05/14 12:46
-	2	jp-06224431\$-\$\$.did.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/05/14 12:47
-	10	jp-302828\$-\$\$.did.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/05/14 12:48
-	2	jp-06302828\$-\$\$.did.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/05/14 12:48
-	2	jp-07226507\$-\$\$.did.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/05/14 12:49
-	2	jp-08255878\$-\$\$.did.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/05/14 12:50

-	0	jp-08255878TR\$-\$\$.did.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/05/14 12:50
-	0	jp-08255878-TR\$-\$\$.did.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/05/14 12:50
-	2	jp-60184681\$-\$\$.did.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/05/14 12:52
-	2	jp-60242678\$-\$\$.did.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/05/14 12:52
-	4	method adj2 using.clm. and optical adj switch.ti.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/05/14 13:29
-	714	(257/295).CCLS.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/05/15 13:13
-	0	("mram.ti,ab.").PN.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/05/15 13:13
-	276	mram.ti,ab.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/05/15 13:21
-	988	((257/295).CCLS.) or mram.ti,ab.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/05/15 13:21
-	873	magnetic adj memory adj device	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/05/15 13:32
-	4	((257/295).CCLS.) or mram.ti,ab. or (magnetic adj memory adj device)) and (ferrimagnetic or ferrimagnet) adj (layer or film)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/05/15 13:38
-	8	((257/295).CCLS.) or mram.ti,ab. or (magnetic adj memory adj device)) and (ferrimagnetic or ferrimagnet) adj2 (layer or film)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/05/15 14:56
-	1	((257/295).CCLS.) or mram.ti,ab. or (magnetic adj memory adj device)) and (ferrimagnetic or ferrimagnet) adj2 (layer or film) same orient\$5	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/05/15 15:06
-	1846	((257/295).CCLS.) or mram.ti,ab. or (magnetic adj memory adj device)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/05/15 17:14

-	2	((257/295).CCLS.) or mram.ti,ab. or (magnetic adj memory adj device)) and data adj (layer or film) near15 (magnetization or magnetisation or magnetized or magnetised) near15 (turn or turning or orientation or orient or oriented)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/15 15:51
-	1	((257/295).CCLS.) or mram.ti,ab. or (magnetic adj memory adj device)) and data adj (layer or film) near15 (magnetization or magnetisation or magnetized or magnetised) near15 (turn or turning or orientation or orient or oriented) and coercivity	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/15 15:59
-	0	((257/295).CCLS.) or mram.ti,ab. or (magnetic adj memory adj device)) and data adj (layer or film) near15 (magnetization or magnetisation or magnetized or magnetised) near15 (turn or turning or orientation or orient or oriented) and coercivity and ferrimagnetic	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/15 17:01
-	719	((257/295).CCLS.) or (magnetic adj memory adj device) and af adj layer	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/15 17:17
-	44	(365/172).CCLS.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/15 17:35
-	283	(365/173).CCLS.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/15 17:35
-	804	((365/171) or (365/172) or (365/173)).CCLS.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/15 18:02
-	0	((365/171) or (365/172) or (365/173)).CCLS.) and (antiferrimagnetic or af) adj (layer of film) and (magnetic adj memory) and coercivity and (data adj storage near3 (layer or film))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/15 18:08
-	4	((365/171) or (365/172) or (365/173)).CCLS.) and (antiferrimagnetic or af) adj (layer of film) and (magnetic adj memory) and coercivity	USPAT; US-PGPUB	2002/05/15 18:10
-	4	((365/171) or (365/172) or (365/173)).CCLS.) and (antiferrimagnetic or af) adj (layer of film) and (magnetic adj memory) and coercivity and (angle or orient or orientation or oriented or turn or turned or turning or rotate or rotated or rotation)	USPAT; US-PGPUB	2002/05/15 19:32
-	0	((365/171) or (365/172) or (365/173)).CCLS.) and ((synthetic adj ferrimagnetic or sf or artificial adj ferrimagnetic) near6 (layer or film))	USPAT; US-PGPUB	2002/05/15 18:31
-	0	((365/171) or (365/172) or (365/173)).CCLS.) and (synthetic adj ferrimagnetic or sf or artificial adj ferrimagnetic)	USPAT; US-PGPUB	2002/05/15 18:31
-	23	(synthetic adj ferrimagnetic or sf or artificial adj ferrimagnetic) and (mram or magnetic adj memory)	USPAT; US-PGPUB	2002/05/15 18:36
-	2	(synthetic adj (ferrimagnet or ferrimagnetic) or sf or artificial adj ferrimagnetic) and (mram or magnetic adj memory).ti,ab.	USPAT; US-PGPUB	2002/05/15 18:38

-	4	((365/171) or (365/172) or (365/173)).CCLS.) and (antiferrimagnetic or femn or af) adj (layer of film) and (magnetic adj memory) and coercivity and (angle or orient or orientation or oriented or turn or turned or turning or rotate or rotated or rotation)	USPAT; US-PGPUB	2002/05/15 19:44
-	4	(antiferrimagnetic or femn or af) adj (layer of film) and (magnetic adj memory) and coercivity and (angle or orient or orientation or oriented or turn or turned or turning or rotate or rotated or rotation)	USPAT; US-PGPUB	2002/05/15 19:46
-	4	(antiferrimagnetic or femn or af) adj (layer of film) and (magnetic adj memory) and coercivity and (angle or orient or orientation or oriented or turn or turned or turning or rotate or rotated or rotation)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/15 19:48
-	4	(antiferrimagnetic or femn or af) adj (layer of film) and (magnetic adj memory) and coercivity	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/15 19:48
-	17	(antiferrimagnetic or femn or af) and (magnetic adj memory) and coercivity	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/15 19:51
-	8934	(antiferrimagnetic or femn or af) and (hs mtj or hard-soft adj mtj)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/15 19:52
-	1	(antiferrimagnetic or femn or af) and (hs adj mtj or hard-soft adj mtj)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/15 21:17
-	1	"5966012".PN.	USPAT	2002/05/15 20:52
-	1	"5841692".PN.	USPAT	2002/05/15 20:55
-	1	"5801984".PN.	USPAT	2002/05/15 20:56
-	1	"5055158".PN.	USPAT	2002/05/15 20:57
-	1	"5055158".PN.	USPAT	2002/05/15 20:58
-	1	(antiferromagnetic or femn or af) and (hs adj mtj or hard-soft adj mtj)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/15 21:24
-	2	("5605958").PN.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/15 21:24
-	3	("5650958").PN.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/15 22:05
-	77	magnetic adj memory and spacer adj layer	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/15 22:29
-	0	magnetic adj memory and (spacer adj layer near12 sf)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/15 22:30

-	77	magnetic adj memory and spacer adj layer	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/05/15 22:48
-	7	magnetic adj memory and (spacer adj layer near5 antiferromagnetic)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/05/16 07:45
-	3	magnetic adj memory and (spacer adj layer near5 antiferromagnetic) and (spacer near12 different)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/05/16 08:01
-	0	(spacer near12 antiferromagnetic near12 different) and magnetic adj2 memory	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/05/16 08:02
-	5	spacer near12 antiferromagnetic near12 different	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/05/16 08:45
-	295	(365/158).CCLS.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/05/16 08:45
-	602	(365/171).CCLS.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/05/16 08:46
-	44	(365/172).CCLS.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/05/16 08:46
-	283	(365/173).CCLS.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/05/16 08:46
-	3429	(365/174).CCLS.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/05/16 08:46
-	431	(257/30).CCLS.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/05/16 08:47
-	4807	((365/158).CCLS.) or ((365/171).CCLS.) or ((365/172).CCLS.) or ((365/173).CCLS.) or ((365/174).CCLS.) or ((257/30).CCLS.)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/05/16 08:47
-	179	spacer and coercivity and antiferromagnetic	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/05/16 08:48
-	11	((365/158).CCLS.) or ((365/171).CCLS.) or ((365/172).CCLS.) or ((365/173).CCLS.) or ((365/174).CCLS.) or ((257/30).CCLS.)) and (spacer and coercivity and antiferromagnetic)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/05/16 13:56

-	5	((((365/158).CCLS.) or ((365/171).CCLS.) or ((365/172).CCLS.) or ((365/173).CCLS.) or ((365/174).CCLS.) or ((257/30).CCLS.)) and (spacer and coercivity and antiferromagnetic)) and @pd<20000104	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/05/16 14:30
-	0	mtj adj mr and world adj line and bottom adj electrode	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/05/16 14:31
-	0	mtj adj mr and world adj line	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/05/16 14:32
-	1	mtj adj mr and word adj line	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/05/16 14:33
-	7	"6114719"	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/05/16 15:30
-	3	mtj and (current near12 (magnetization or magnetized)) near12 (perpendicular or orthogonal)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/05/16 16:37
-	0	"not pinned" and (mram or mtj)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/05/16 16:44
-	0	"not pinned" and (mram or mtj or magneto-resistive or af adj layer)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/05/16 16:45
-	178	(hard same soft) and (mram or mtj or magneto-resistive or af adj layer)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/05/16 16:47
-	0	(soft-soft) and (mram or mtj or magneto-resistive or af adj layer)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/05/16 16:47
-	0	soft-soft and (mtj or mram or magneto-resistive)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/05/16 16:49
-	11	soft-soft	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/05/16 16:50
-	0	soft-soft and magnetic	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/05/16 16:50
-	3	mtj and second adj free	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/05/16 20:54

-	17	(spacer near12 (ru or ruthenium)) near12 (af adj layer reference adj layer or data adj layer or sens\$3 adj layer or pinned adj2 layer)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB USPAT	2002/05/16 22:40
-	3	((("5640343") or ("6269018") or ("5966012"))).PN.		2002/05/16 23:13
-	2	903452.ap.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB USPAT	2002/11/04 11:23
-	2	("5989958").PN.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB USPAT	2002/11/04 12:57
-	0	jp-03571261\$-\$.did.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB USPAT	2002/11/04 12:58
-	8	hamakawa.in. and silicon and carbide and semiconductor	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB JPO	2002/11/04 13:00
-	2	"3571261"	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB USPAT	2002/11/04 12:59
-	1	"carbide/amorphous".ti.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB USPAT	2002/11/04 15:49
-	0	optoelectric adj conversion and electron adj affinity	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB USPAT	2002/11/04 18:04
-	329	optoelectric adj conversion	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB USPAT	2002/11/04 18:04
-	2724	electron adj affinity	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB USPAT	2002/11/04 18:04
-	0	optoelectric adj conversion near12 affinity	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB USPAT	2002/11/04 18:05
-	32	optoelectric adj conversion near12 efficiency	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB USPAT	2002/11/04 18:06
-	4	optoelectric adj conversion near12 efficiency and silicon adj carbide	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB USPAT	2002/11/04 18:07
-	3404	((257/77) or (257/314) or (257/315) or (257/316)).CCLS.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB USPAT	2002/11/05 11:44

-	14	((257/77) or (257/314) or (257/315) or (257/316)).CCLS.) and breakdown adj voltage near15 silicon adj carbide	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/11/05 11:46
-	1	((257/77) or (257/314) or (257/315) or (257/316)).CCLS.) and electron adj affinity near15 silicon adj carbide	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/11/05 11:47
-	2	("6104054").PN.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/11/05 14:24
-	8	("5661312") or ("5798548") or ("5989958") or ("5808336") or ("5369040") or ("5557122") or ("5393999") or ("5734181").PN.	USPAT	2003/01/27 10:34
-	0	jp-357126175\$-\$\$.did.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/01/27 10:38
-	2	jp-57126175\$-\$\$.did.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/01/27 10:40
-	2	jp-02203564\$-\$\$.did.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/01/27 10:40
-	13	(US-6084248-\$ or US-6031263-\$ or US-5976926-\$ or US-5858811-\$ or US-5698869-\$ or US-4473836-\$ or US-4113515-\$ or US-6130147-\$ or US-6144581-\$ or US-6099574-\$ or US-6093937-\$ or US-6166401-\$ or US-6163066-\$).did.	USPAT	2003/03/21 13:50
-	57	hamakawa.in. and conversion	USPAT; JPO	2003/03/21 13:51
-	0	hamakawa.in. and conversion and optoelectronic	JPO	2003/03/21 13:51
-	1	hamakawa.in. and conversion and heterojunction	JPO	2003/03/21 13:52
-	31	hamakawa.in. and conversion	JPO	2003/03/21 13:52

-	141	(US-5449941-\$ or US-6383576-\$ or US-6166319-\$ or US-5451798-\$ or US-5734181-\$ or US-5260560-\$ or US-5886379-\$ or US-5786250-\$ or US-5877041-\$ or US-5846859-\$ or US-5789276-\$ or US-5754477-\$ or US-5740104-\$ or US-5670790-\$ or US-5714766-\$ or US-5654208-\$ or US-5623442-\$ or US-5580380-\$ or US-5604357-\$ or US-5562769-\$ or US-5557114-\$ or US-5530581-\$ or US-5477485-\$ or US-5455432-\$ or US-5407845-\$ or US-5415126-\$).did. or (US-5298796-\$ or US-5293560-\$ or US-5260593-\$ or US-5235195-\$ or US-5145741-\$ or US-5111430-\$ or US-5049950-\$ or US-4893273-\$ or US-4841349-\$ or US-4769686-\$ or US-4738729-\$ or US-4657699-\$ or US-4462150-\$ or US-4460670-\$ or US-6002143-\$ or US-5852306-\$ or US-4849797-\$ or US-5369040-\$ or US-5039354-\$ or US-5159424-\$ or US-5056897-\$ or US-4826778-\$ or US-5886368-\$ or US-5719410-\$ or US-5371383-\$ or US-6236590-\$ or US-6166948-\$).did. or (US-5793697-\$ or US-5640343-\$ or US-6205052-\$ or US-6178112-\$ or US-6197439-\$ or US-6108177-\$ or US-5408377-\$ or US-6365919-\$ or US-6313482-\$ or US-6306691-\$ or US-6249020-\$ or US-6018166-\$ or US-6133587-\$ or US-6121633-\$ or US-6075259-\$ or US-6049110-\$ or US-6011279-\$ or US-5798548-\$ or US-5661312-\$ or US-5539217-\$ or US-5465249-\$ or US-5323040-\$ or US-4507673-\$ or US-5625217-\$ or US-5061976-\$ or US-6344663-\$ or US-6180958-\$).did. or (US-5989958-\$ or US-5801401-\$ or US-5393999-\$ or US-5629222-\$ or US-6309907-\$ or US-4768072-\$ or US-4451391-\$ or US-6351411-\$ or US-5898197-\$ or US-5508543-\$ or US-5808336-\$ or US-5866930-\$ or US-5557122-\$ or US-6034001-\$ or US-5907775-\$ or US-6166401-\$ or US-6163066-\$ or US-6144581-\$ or US-6093937-\$ or US-6099574-\$ or US-6130147-\$ or US-6031263-\$ or US-6084248-\$ or US-5976926-\$ or US-5698869-\$ or US-4113515-\$ or US-4473836-\$).did. or (US-5858811-\$).did. or (US-20020017647-\$ or US-20020036331-\$ or US-20020041514-\$ or US-20020024050-\$ or US-20010049183-\$ or US-20010032997-\$).did. or (EP-291951-\$ or US-5585986-\$ or EP-681333-\$).did. or (JP-63219172-\$ or JP-01115162-\$ or JP-06302828-\$ or JP-07226507-\$ or JP-08255878-\$ or JP-60184681-\$ or JP-60242678-\$ or JP-63181473-\$ or JP-62122275-\$ or JP-04056769-\$ or JP-03222367-\$ or JP-02203564-\$ or JP-56056677-\$ or JP-04061170-\$ or JP-57126175-\$ or JP-06224431-\$ or JP-63289960-\$).did. or (EP-276002-\$ or JP-07115191-\$ or JP-62122275-\$ or JP-60184681-\$ or JP-01115162-\$ or JP-04056769-\$ or US-6081446-\$ or EP-291951-\$).did.	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/03/25 11:00
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-	1	((US-5449941-\$ or US-6383576-\$ or US-6166319-\$ or US-5451798-\$ or US-5734181-\$ or US-5260560-\$ or US-5886379-\$ or US-5786250-\$ or US-5877041-\$ or US-5846859-\$ or US-5789276-\$ or US-5754477-\$ or US-5740104-\$ or US-5670790-\$ or US-5714766-\$ or US-5654208-\$ or US-5623442-\$ or US-5580380-\$ or US-5604357-\$ or US-5562769-\$ or US-5557114-\$ or US-5530581-\$ or US-5477485-\$ or US-5455432-\$ or US-5407845-\$ or US-5415126-\$).did. or (US-5298796-\$ or US-5293560-\$ or US-5260593-\$ or US-5235195-\$ or US-5145741-\$ or US-5111430-\$ or US-5049950-\$ or US-4893273-\$ or US-4841349-\$ or US-4769686-\$ or US-4738729-\$ or US-4657699-\$ or US-4462150-\$ or US-4460670-\$ or US-6002143-\$ or US-5852306-\$ or US-4849797-\$ or US-5369040-\$ or US-5039354-\$ or US-5159424-\$ or US-5056897-\$ or US-4826778-\$ or US-5886368-\$ or US-5719410-\$ or US-5371383-\$ or US-6236590-\$ or US-6166948-\$).did. or (US-5793697-\$ or US-5640343-\$ or US-6205052-\$ or US-6178112-\$ or US-6197439-\$ or US-6108177-\$ or US-5408377-\$ or US-6365919-\$ or US-6313482-\$ or US-6306691-\$ or US-6249020-\$ or US-6018166-\$ or US-6133587-\$ or US-6121633-\$ or US-6075259-\$ or US-6049110-\$ or US-6011279-\$ or US-5798548-\$ or US-5661312-\$ or US-5539217-\$ or US-5465249-\$ or US-5323040-\$ or US-4507673-\$ or US-5625217-\$ or US-5061976-\$ or US-6344663-\$ or US-6180958-\$).did. or (US-5989958-\$ or US-5801401-\$ or US-5393999-\$ or US-5629222-\$ or US-6309907-\$ or US-4768072-\$ or US-4451391-\$ or US-6351411-\$ or US-5898197-\$ or US-5508543-\$ or US-5808336-\$ or US-5866930-\$ or US-5557122-\$ or US-6034001-\$ or US-5907775-\$ or US-6166401-\$ or US-6163066-\$ or US-6144581-\$ or US-6093937-\$ or US-6099574-\$ or US-6130147-\$ or US-6031263-\$ or US-6084248-\$ or US-5976926-\$ or US-5698869-\$ or US-4113515-\$ or US-4473836-\$).did. or (US-5858811-\$).did. or (US-20020017647-\$ or US-20020036331-\$ or US-20020041514-\$ or US-20020024050-\$ or US-20010049183-\$ or US-20010032997-\$).did. or (EP-291951-\$ or US-5585986-\$ or EP-681333-\$).did. or (JP-63219172-\$ or JP-01115162-\$ or JP-06302828-\$ or JP-07226507-\$ or JP-08255878-\$ or JP-60184681-\$ or JP-60242678-\$ or JP-63181473-\$ or JP-62122275-\$ or JP-04056769-\$ or JP-03222367-\$ or JP-02203564-\$ or JP-56056677-\$ or JP-04061170-\$ or JP-57126175-\$ or JP-06224431-\$ or JP-63289960-\$).did. or (EP-276002-\$ or JP-07115191-\$ or JP-62122275-\$ or JP-60184681-\$ or JP-01115162-\$ or JP-04056769-\$ or US-6081446-\$ or EP-291951-\$).did.) and miyawaki.in.	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/03/25 11:00
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-	1	("4460670").PN.	USPAT	2003/03/25 17:05
-	1	("4462150").PN.	USPAT	2003/03/25 17:05
-	10	(transistor MOS MOSFET) and gate near12 ("Si.sub.1-x C.sub.x" silicon adj carbide near12 (x or y))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/08/18 17:38
-	11	(transistor MOS MOSFET) and gate near12 ("Si.sub.1-x C.sub.x" "Si.sub.x C.sub.1-x" "Si.sub.1-y C.sub.y" "Si.sub.y C.sub.1-y" silicon adj carbide near12 (x or y))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/08/18 17:35
-	1	((transistor MOS MOSFET) and gate near12 ("Si.sub.1-x C.sub.x" "Si.sub.x C.sub.1-x" "Si.sub.1-y C.sub.y" "Si.sub.y C.sub.1-y" silicon adj carbide near12 (x or y))) not ((transistor MOS MOSFET) and gate near12 ("Si.sub.1-x C.sub.x" silicon adj carbide near12 (x or y)))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/08/18 17:35
-	8	gate near12 ("Si.sub.1-x C.sub.x" silicon adj carbide near12 (x or y)) and 257/\$9.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/08/18 17:40
-	0	(gate near12 ("Si.sub.1-x C.sub.x" silicon adj carbide near12 (x or y)) and 257/\$9.ccls.) not ((transistor MOS MOSFET) and gate near12 ("Si.sub.1-x C.sub.x" "Si.sub.x C.sub.1-x" "Si.sub.1-y C.sub.y" "Si.sub.y C.sub.1-y" silicon adj carbide near12 (x or y)))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/08/18 17:39
-	10	gate near12 ("Si.sub.1-x C.sub.x" silicon adj carbide near12 (x or y))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/08/18 17:40
-	0	(gate near12 ("Si.sub.1-x C.sub.x" silicon adj carbide near12 (x or y))) not ((transistor MOS MOSFET) and gate near12 ("Si.sub.1-x C.sub.x" "Si.sub.x C.sub.1-x" "Si.sub.1-y C.sub.y" "Si.sub.y C.sub.1-y" silicon adj carbide near12 (x or y)))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/08/18 18:18
-	2	("5661312").PN.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/08/19 09:13
-	0	("jp-57125175\$-\$\$.did.").PN.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/08/19 09:14
-	0	jp-57125175\$-\$\$.did.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/08/19 09:14
-	2	jp-57126175\$-\$\$.did.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/08/19 10:49
-	229	barrier near6 gate and silicon adj carbide	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/08/19 09:35
-	5	barrier near6 gate near6 silicon adj carbide	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/08/19 10:02

-	1	"5506421".PN.	USPAT	2003/08/19 09:37
-	1	"5495124".PN.	USPAT	2003/08/19 09:39
-	1	"5451797".PN.	USPAT	2003/08/19 09:39
-	1	"5396085".PN.	USPAT	2003/08/19 09:43
-	1	"5393999".PN.	USPAT	2003/08/19 09:45
-	15	gate near6 breakdown near6 (silicon adj carbide "Si.sub.1-x" adj "C.sub.x" "Si.sub.x" adj "C.sub.1-x")	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/08/19 10:12
-	304	"Si.sub.1-x" adj "C.sub.x" "Si.sub.x" adj "C.sub.1-x"	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/08/19 10:13
-	12	("Si.sub.1-x" adj "C.sub.x" "Si.sub.x" adj "C.sub.1-x") and gate near6 breakdown	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/08/19 10:14
-	2	("5369040").PN.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/08/19 10:58
-	0	("MOSadjphotodetector.ti,ab.").PN.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/08/19 10:58
-	8	MOS adj photodetector.ti,ab.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/08/19 11:50
-	17	gate near6 polysilicon near6 carbon	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/08/19 12:12
-	1	"4963953".PN.	USPAT	2003/08/19 12:03
-	1	"4780394".PN.	USPAT	2003/08/19 12:04
-	1	"4352237".PN.	USPAT	2003/08/19 12:04
-	1	"4189826".PN.	USPAT	2003/08/19 12:04
-	4	("3497773"   "3622382"   "3728590"   "3896485").PN.	USPAT	2003/08/19 12:07
-	43	3896485.URPN.	USPAT	2003/08/19 12:07
-	1	MOS adj photodetector.ti,ab,clm. and source and channel and drain	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/08/19 12:13
-	1	(MOS MOSFET) adj photodetector.ti,ab,clm. and source and channel and drain	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/08/19 12:16
-	395	photodetector.ti,ab,clm. and source and channel and drain	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/08/19 12:17
-	100	photodetector.ti,ab,clm. and source near20 channel near20 drain near20 gate	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/08/19 12:17
-	0	photodetector.ti,ab,clm. and source near20 channel near20 drain near20 gate near20 (sic silicon adj carbide)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/08/19 12:19

-	1	photodetector.ti,ab,clm. and source near20 channel near20 drain near20 gate near20 polysilicon	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/08/19 12:23
-	7	photodetector.ti,ab,clm. and source near20 channel near20 drain near20 gate near20 (silicon polysilicon)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/08/19 13:12
-	2	("5808336").PN.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/08/19 13:13
-	51	floating adj gate and photodetector and source and drain and channel	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/08/19 13:55
-	65	double-poly near12 gate	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/08/19 15:12
-	0	"4963953".PN.	USPAT	2003/08/19 15:07
-	21	((("3792465") or ("4118795") or ("4384349") or ("4816883") or ("4897710") or ("5317535") or ("5366713") or ("5388069") or ("5424993") or ("5438544") or ("5441901") or ("5467306") or ("5493140") or ("5672889") or ("5828101") or ("5861346") or ("5912837") or ("5926740") or ("6297521") or ("6307775") or ("6309907"))).PN.	USPAT	2003/08/19 15:29
-	9	((("3792465") or ("4118795") or ("4384349") or ("4816883") or ("4897710") or ("5317535") or ("5366713") or ("5388069") or ("5424993") or ("5438544") or ("5441901") or ("5467306") or ("5493140") or ("5672889") or ("5828101") or ("5861346") or ("5912837") or ("5926740") or ("6297521") or ("6307775") or ("6309907"))).PN.) and (silicon adj carbide or carbon near3 (polysilicon silicon))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/08/19 16:01
-	122	silicon adj carbide and monocrystalline and power adj2 (MOS MOSFET device)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/08/19 16:02
-	59	silicon adj carbide near12 monocrystalline and power adj2 (MOS MOSFET device)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/08/19 16:02
-	13	silicon adj carbide near12 monocrystalline and power adj2 (MOS MOSFET device).ti,ab,clm.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/08/19 16:04
-	1430	silicon adj carbide near6 (MOS MOSFET device).ti,ab,clm.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/08/19 16:05
-	111	silicon adj carbide near6 power near6 (MOS MOSFET device).ti,ab,clm.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/08/19 16:05

-	55	silicon adj carbide near6 power near6 (MOS MOSFET).ti,ab,clm.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/08/19 16:05
-	6	silicon adj carbide near6 power near6 (MOS MOSFET).ti,ab,clm. and monocrystalline near6 silicon adj carbide	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/08/19 16:15
-	1811	amorphous adj silicon adj carbide	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/08/19 16:16
-	73	amorphous adj silicon adj carbide and grain adj size	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/08/19 16:16
-	2	amorphous adj silicon adj carbide near12 grain adj size	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/08/19 16:32
-	23	epitaxial\$2 near12 silicon adj carbide near12 method and (monocrystal monocrystalline)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/08/19 16:34
-	5	epitaxial\$2 near12 silicon adj carbide near12 method near12 (monocrystal monocrystalline)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/08/19 16:35
-	463	method near12 epitaxial\$2 near12 (monocrystal monocrystalline)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/08/19 16:38
-	112	method near12 epitaxial\$2 near12 (monocrystal monocrystalline) and 117/\$6.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/08/19 16:59
-	112	method near12 epitaxial\$2 near12 crystallinity	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/08/19 16:59
-	0	method near12 epitaxial\$2 near12 crystallinity and silicon adj carbide	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/08/19 17:00
-	0	method near12 epitaxial\$2 near12 ensur\$3 near12 crystallinity	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/08/19 17:00
-	49	monocrystalline near4 silicon adj carbide and power.ti,ab,clm.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/08/19 17:01
-	2	monocrystalline near4 silicon adj carbide near6 breakdown and power.ti,ab,clm.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/08/19 17:02

-	2	("5,449,925").PN.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/08/19 17:02
-	2	("5449925").PN.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/08/19 17:03
-	1	(("5449925").PN.) and epitaxial\$3	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/08/19 17:05
-	10	epitaxial\$3 near6 grow\$3 near6 monocrystalline near6 silicon adj carbide	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/08/19 17:08
-	14	grow\$3 near6 monocrystalline near6 silicon adj carbide.ti,ab,clm.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/08/19 17:08
-	3	method near6 grow\$3 near6 monocrystalline near6 silicon adj carbide.ti,ab,clm.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/08/19 17:09
-	1	method near6 grow\$3 near6 monocrystalline near6 silicon adj carbide.ti,ab,clm. and power.ti,ab,clm.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/08/19 17:09
-	16	method near6 (growth growing) near6 (monocrystalline monocystal) near12 (silicon adj carbide sic)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/08/19 17:11
-	13	method near6 (growth growing) near6 (monocrystalline monocystal) near12 (silicon adj carbide sic) and epitaxial\$2	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/08/19 17:20
-	2	jp-57126175\$-\$.did.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/08/19 17:25
-	13	epitaxy near6 (grain crystal) adj size	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/08/19 17:39
-	4	(work adj function workfunction) near12 crystallinity	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/08/19 17:41
-	184995	(work adj function workfunction) near12 silicon carbide	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/08/19 17:41
-	15	(work adj function workfunction) near12 silicon adj carbide	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/08/19 17:43

-	15	(work adj function workfunction) near12 crystalline near6 amorphous	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/08/19 17:58
-	0	("carbonadjgate").PN.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/08/19 17:59
-	9657	gate adj gate	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/08/19 17:59
-	0	carbon adj gate and source and drain	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/08/19 18:00
-	23	carbon adj gate	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/08/19 18:00
-	19	carbon adj gate and (257/\$9.ccls. 117/\$9.ccls. 438/\$9.ccls.)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/08/19 18:03
-	14	"carbon gate" and (257/\$9.ccls. 117/\$9.ccls. 438/\$9.ccls.)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/08/19 18:04
-	63	("si.sub.x" adj "c.sub.1-x" or "si.sub.1-x" adj "c.sub.x") and (energy adj gap or band adj energy)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/08/20 10:00